

**Major Ratings and Characteristics**

$I_{F(AV)}$	1.0 A
$V_{RRM}$	50 V to 600 V
$I_{FSM}$	30 A
$t_{rr}$	35 nS
$V_F$	0.95 V, 1.3 V, 1.7 V
$T_j \text{ max.}$	150 °C



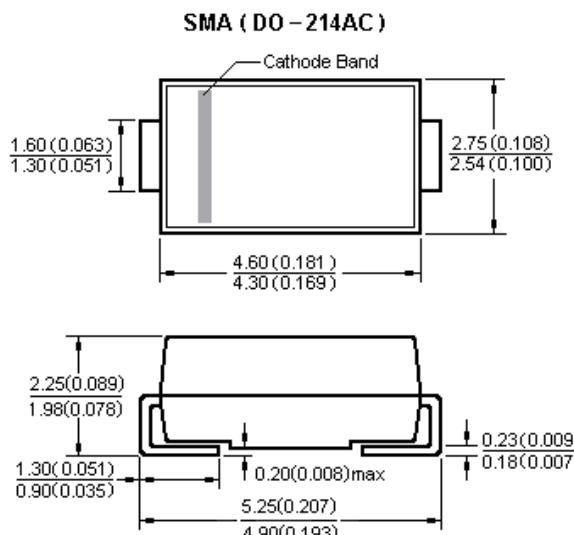
SMA (DO-214AC)

**Features**

- Glass passivated chip junction
- Ideal for automated placement
- Ultrafast reverse recovery time for high efficiency
- Low profile package
- High forward surge capability
- High temperature soldering:  
260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/1  
and WEEE 2002/96/EC

**Mechanical Data**

- Case: JEDEC DO-214AC molded plastic body over passivated chip
- Terminals: Solder plated, solderable per J-STD-002B and JESD22-B102D
- Polarity: Laser band denotes cathode end



Dimensions in millimeters and (inches)

**Maximum Ratings & Thermal Characteristics & Electrical Characteristics**

(TA = 25 °C unless otherwise noted)

	Symbol	(ES1A)	(ES1A)	(ES1D)	(ES1G)	(ES1J)	UNIT
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	200	400	600	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	V
Maximum average forward rectified current	$I_{F(AV)}$				1		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$				30		A
Maximum instantaneous forward voltage at 1.0A	$V_F$		0.95		1.30	1.70	V
Maximum DC reverse current TA = 25 °C at Rated DC blocking voltage TA = 100°C	$I_R$			5.0			µA
				100			µA
Maximum reverse recovery time at $I_F = 0.5 \text{ A}$ , $I_R = 1.0 \text{ A}$ , $I_{rr} = 0.25 \text{ A}$	$t_{rr}$			35			nS
Typical junction capacitance at 4.0 V ,1MHz	$C_J$			15			p F
Typical thermal resistance	$R_{\theta JA}$			75			°C/ W
Operating junction and storage temperature range	$T_J$ , $T_{STG}$			-55 to +150			°C

# (ES1A~ES1J)SMA

Super Fast recovery rectifiers

**YFW**  
佑风微

Characteristic Curves ( $T_A=25^\circ\text{C}$  unless otherwise noted)

